TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA562TM

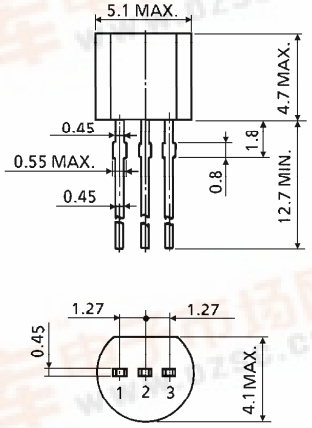
AUDIO FREQUENCY LOW POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

SWITCHING APPLICATIONS

- Excellent h_{FE} Linearity.
  $h_{FE\,(2)}$ = 25 (Min.) at V_{CE} = −6V, I_C = −400mA
- 1 Watt Amplifier Application.
- Complementary to 2SC1959.

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	TO-92
EIAJ	SC-43
TOSHIBA	2-5F1B

Weight : 0.21g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	−35	V
Collector-Emitter Voltage	V_{CEO}	−30	V
Emitter-Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−500	mA
Base Current	I_B	−100	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

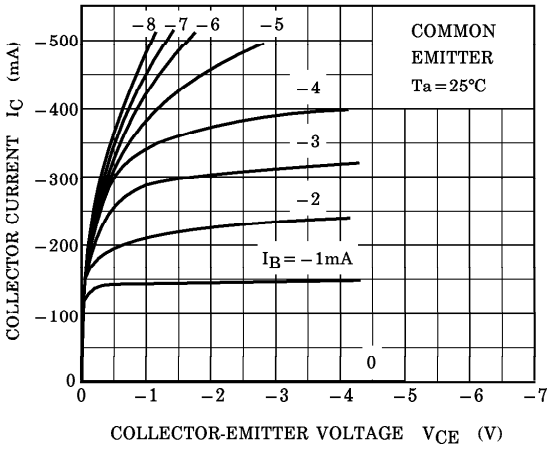
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = −35V, I_E = 0	—	—	−0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = −5V, I_C = 0	—	—	−0.1	μA
DC Current Gain	$h_{FE\,(1)}$ (Note)	V_{CE} = −1V, I_C = −100mA	70	—	240	
	$h_{FE\,(2)}$ (Note)	V_{CE} = −6V, I_C = −400mA	25	—	—	
Collector-Emitter Saturation Voltage	$V_{CE\,(sat)}$	I_C = −100mA, I_B = −10mA	—	−0.1	−0.25	V
Base-Emitter Voltage	V_{BE}	V_{CE} = −1V, I_C = −100mA	—	−0.8	−1.0	V
Transition Frequency	f_T	V_{CE} = −6V, I_C = −20mA	—	200	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = −6V, I_E = 0, f = 1MHz	—	13	—	pF

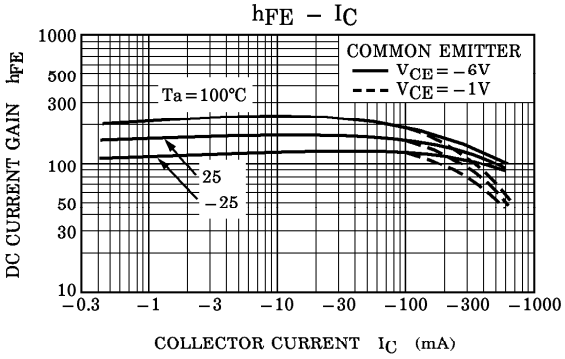
Note : $h_{FE\,(1)}$ Classification O : 70~140, Y : 120~240
$h_{FE\,(2)}$ Classification O : 25 (Min.), Y : 40 (Min.)

961001EAA2

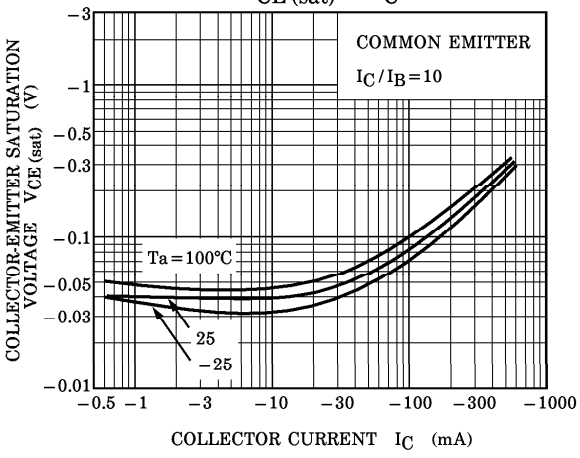
$I_C - V_{CE}$



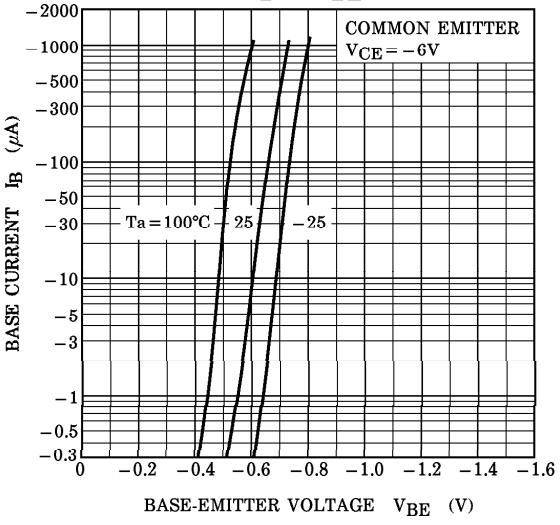
$h_{FE} - I_C$



$V_{CE\,(sat)} - I_C$



$I_B - V_{BE}$



$P_C - Ta$